

# Protection Device

TVS (Transient Voltage Suppressor)

## ESD221-U1-02EL

Uni-directional, 5.3 V, 38 pF, 0402, RoHS and Halogen Free compliant

ESD221-U1-02EL

## Data Sheet

Revision 1.0, 2014-05-20  
Final

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## 1 Product Overview

### 1.1 Features

- ESD / transient protection of data and  $V_{BUS}$  lines according to:
  - IEC61000-4-2 (ESD):  $\pm 25$  kV (air)  $\pm 20$  kV (contact)
  - IEC61000-4-4 (EFT):  $\pm 2.5$  kV /  $\pm 50$  A (5/50 ns)
  - IEC61000-4-5 (Surge):  $\pm 5.5$  A (8/20  $\mu$ s)
- Uni-directional, working voltage up to  $V_{RWM} = \pm 5.3$  V
- Medium capacitance:  $C_L = 38$  pF (typical)
- Very low clamping voltage  $V_{CL} = +10 / -5$  V (typical) at  $I_{TLP} = 16$  A
- Low reverse current  $I_R < 100$  nA at  $V_R = 3.3$  V
- Pb-free (RoHS compliant) and halogen free package



### 1.2 Application Examples

- $V_{BUS}$  line protection in USB ports
- Keypad, touchpad, buttons, convenience keys
- LCD displays, Camera, audio lines, mobile communication, Consumer products (E-Book, MP3, DVD, DSC...)
- Notebooks tablets and desktop computers and their peripherals

### 1.3 Product Description

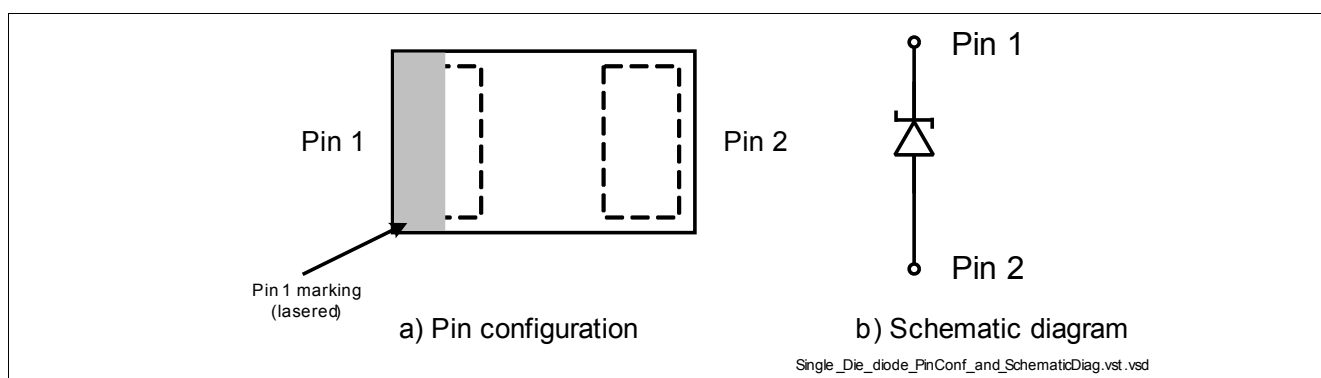


Figure 1-1 Pin Configuration and Schematic Diagram

Table 1-1 Part Information

| Type           | Package   | Configuration           | Marking code |
|----------------|-----------|-------------------------|--------------|
| ESD221-U1-02EL | TSLP-2-19 | 1 line, uni-directional | E            |

## 2 Maximum Ratings

**Table 2-1 Maximum Ratings** at  $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

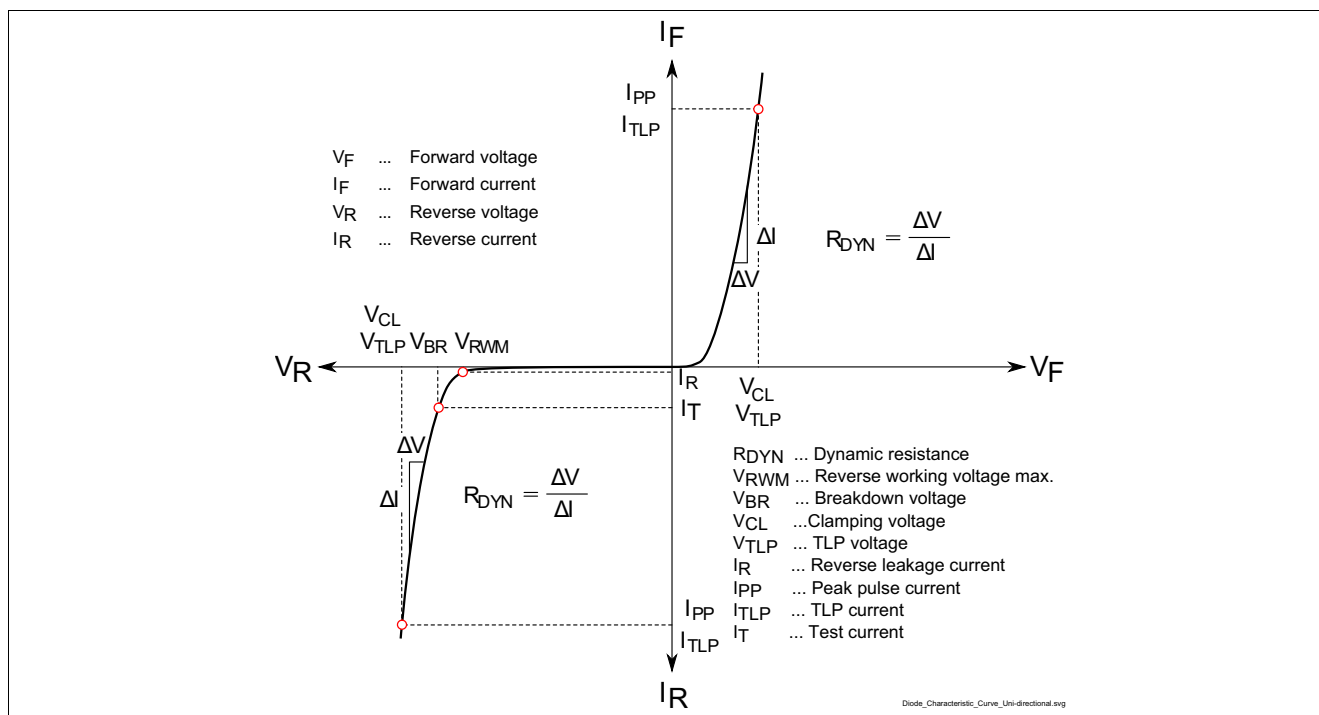
| Parameter                           | Symbol           | Values     | Unit               |
|-------------------------------------|------------------|------------|--------------------|
| ESD air discharge <sup>1)</sup>     | $V_{\text{ESD}}$ | $\pm 25$   | kV                 |
| ESD contact discharge <sup>1)</sup> |                  | $\pm 20$   |                    |
| Peak pulse power <sup>2)</sup>      | $P_{\text{PK}}$  | 60         | W                  |
| Peak pulse current <sup>2)</sup>    | $I_{\text{PP}}$  | $\pm 5.5$  | A                  |
| Operating temperature range         | $T_{\text{OP}}$  | -55 to 125 | $^{\circ}\text{C}$ |
| Storage temperature                 | $T_{\text{stg}}$ | -65 to 150 | $^{\circ}\text{C}$ |

1)  $V_{\text{ESD}}$  according to IEC61000-4-2

2) Non-repetitive current pulse 8/20 $\mu\text{s}$  exponential decay waveform according to IEC61000-4-5

**Attention:** Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

## 3 Electrical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified



**Figure 3-1 Definitions of electrical characteristics**

### Electrical Characteristics at $T_A = 25^\circ\text{C}$ , unless otherwise specified

**Table 3-1 DC Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

| Parameter               | Symbol    | Values |      |      | Unit | Note / Test Condition |
|-------------------------|-----------|--------|------|------|------|-----------------------|
|                         |           | Min.   | Typ. | Max. |      |                       |
| Reverse working voltage | $V_{RWM}$ | –      | –    | 5.3  | V    | from Pin 1 to Pin 2   |
| Breakdown voltage       | $V_{BR}$  | 5.7    | 6.4  | 7.5  | V    | $I_T = 1\text{ mA}$   |
| Reverse current         | $I_R$     | –      | –    | 100  | nA   | $V_R = 3.3\text{ V}$  |

**Table 3-2 AC Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

| Parameter         | Symbol | Values |      |      | Unit | Note / Test Condition                  |
|-------------------|--------|--------|------|------|------|----------------------------------------|
|                   |        | Min.   | Typ. | Max. |      |                                        |
| Line capacitance  | $C_L$  | –      | 38   | –    | pF   | $V_R = 0\text{ V}, f = 1\text{ MHz}$   |
|                   |        | –      | 20   | –    |      | $V_R = 2.5\text{ V}, f = 1\text{ MHz}$ |
| Series inductance | $L_S$  | –      | 0.4  | –    | nH   |                                        |

**Table 3-3 ESD and Surge Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

| Parameter                        | Symbol    | Values |      |      | Unit     | Note / Test Condition                                                      |
|----------------------------------|-----------|--------|------|------|----------|----------------------------------------------------------------------------|
|                                  |           | Min.   | Typ. | Max. |          |                                                                            |
| Clamping voltage <sup>1)</sup>   | $V_{CL}$  | –      | 10   | –    | V        | $I_{TLP} = 16\text{ A}, t_p = 100\text{ ns}$ ,<br>Pin 1 to Pin 2           |
|                                  |           | –      | 14   | –    |          | $I_{TLP} = 30\text{ A}, t_p = 100\text{ ns}$ ,<br>Pin 1 to Pin 2           |
|                                  |           | –      | 5    | –    |          | $I_{TLP} = 16\text{ A}, t_p = 100\text{ ns}$ ,<br>Pin 2 to Pin 1           |
|                                  |           | –      | 7    | –    |          | $I_{TLP} = 30\text{ A}, t_p = 100\text{ ns}$ ,<br>Pin 2 to Pin 1           |
| Clamping voltage <sup>2)</sup>   | $V_{CL}$  | –      | 7    | 9    |          | $I_{PP} = 1\text{ A}, t_p = 8/20\text{ }\mu\text{s}$ ,<br>Pin 1 to Pin 2   |
|                                  |           | –      | 8    | 10   |          | $I_{PP} = 3.5\text{ A}, t_p = 8/20\text{ }\mu\text{s}$ ,<br>Pin 1 to Pin 2 |
|                                  |           | –      | 9    | 11   |          | $I_{PP} = 5.5\text{ A}, t_p = 8/20\text{ }\mu\text{s}$ ,<br>Pin 1 to Pin 2 |
|                                  |           | –      | 1.2  | 2    |          | $I_{PP} = 1\text{ A}, t_p = 8/20\text{ }\mu\text{s}$ ,<br>Pin 2 to Pin 1   |
|                                  |           | –      | 2    | 3    |          | $I_{PP} = 3.5\text{ A}, t_p = 8/20\text{ }\mu\text{s}$ ,<br>Pin 2 to Pin 1 |
|                                  |           | –      | 2.5  | 3.5  |          | $I_{PP} = 5.5\text{ A}, t_p = 8/20\text{ }\mu\text{s}$ ,<br>Pin 2 to Pin 1 |
| Dynamic resistance <sup>1)</sup> | $R_{DYN}$ | –      | 0.3  | –    | $\Omega$ | $t_p = 100\text{ ns}$                                                      |

1) Please refer to Application Note AN210[1] TLP parameter:  $Z_0 = 50\text{ }\Omega$ ,  $t_p = 100\text{ ns}$ ,  $t_r = 300\text{ ps}$ .

2) Non-repetitive current pulse 8/20 $\mu\text{s}$  exponential decay waveform according to IEC61000-4-5

## 4 Typical Characteristics Diagrams

Typical characteristics diagrams at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

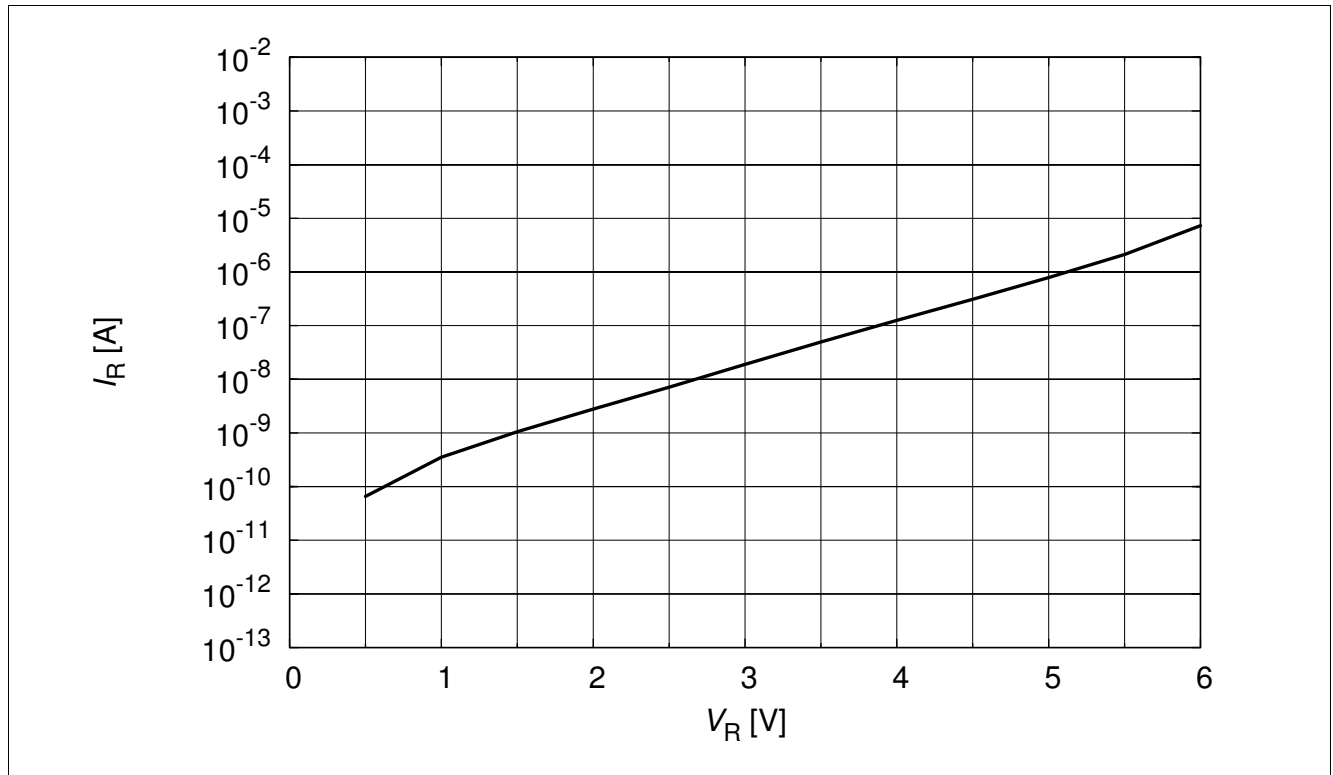


Figure 4-1 Reverse leakage current:  $I_R = f(V_R)$

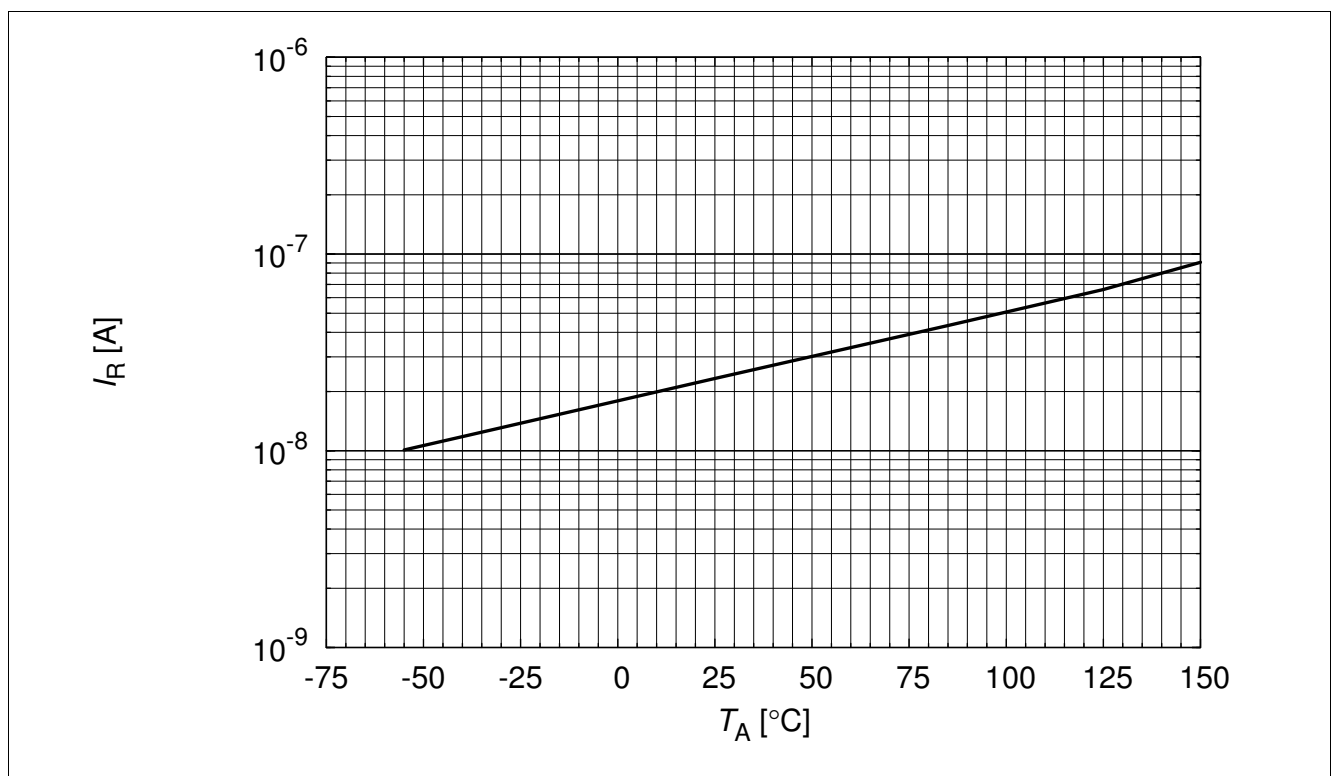


Figure 4-2 Reverse leakage current:  $I_R = f(T_A)$ ,  $V_R = 3.3$  V

# Typical Characteristics Diagrams

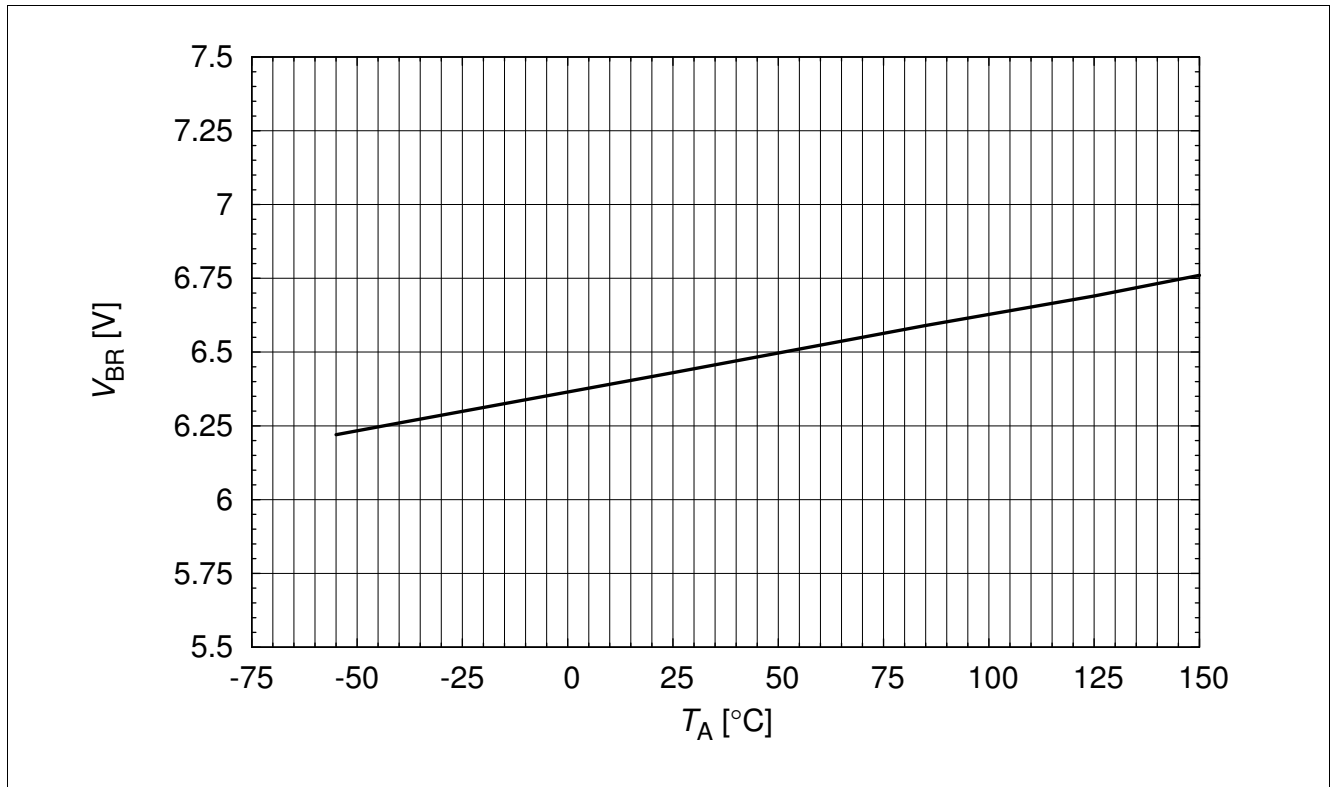


Figure 4-3 Breakdown voltage:  $V_{BR} = f(T_A)$ ,  $I_R = 1$  mA

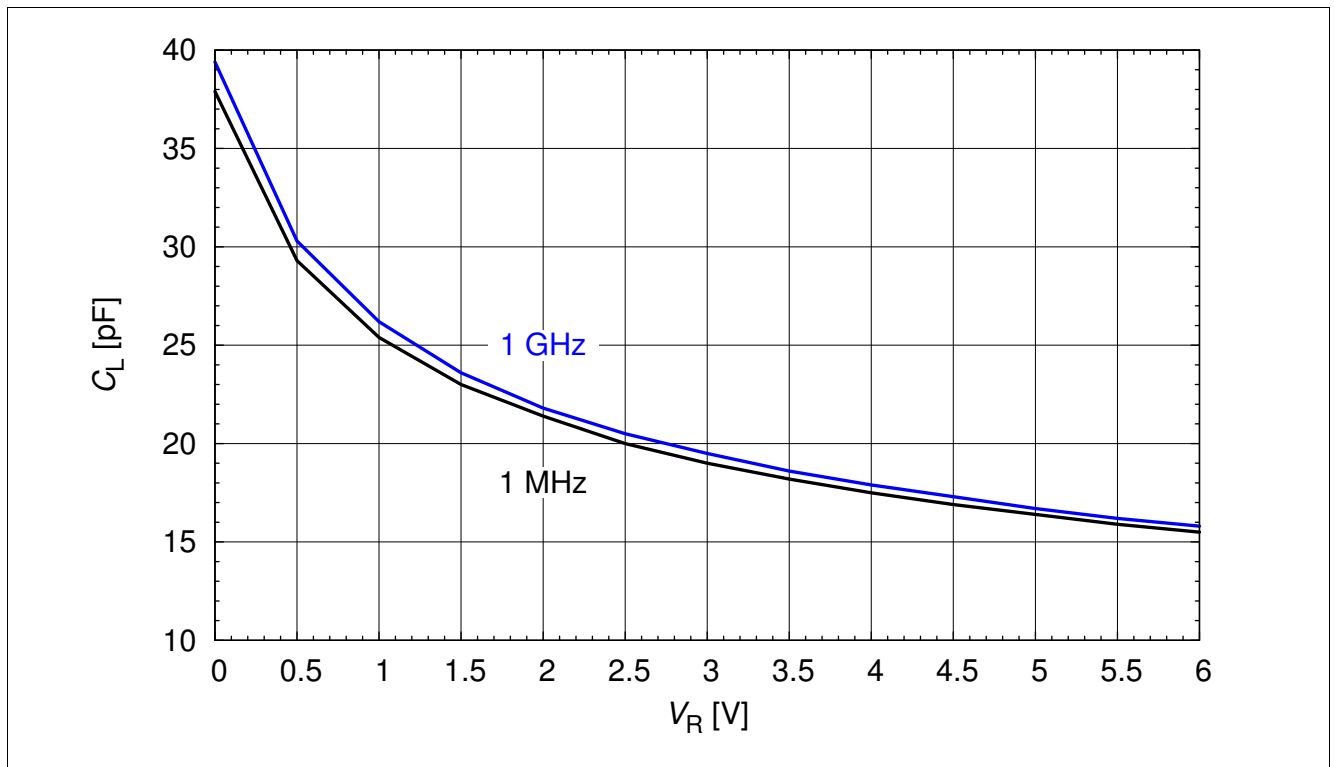


Figure 4-4 Line capacitance:  $C_L = f(V_R)$

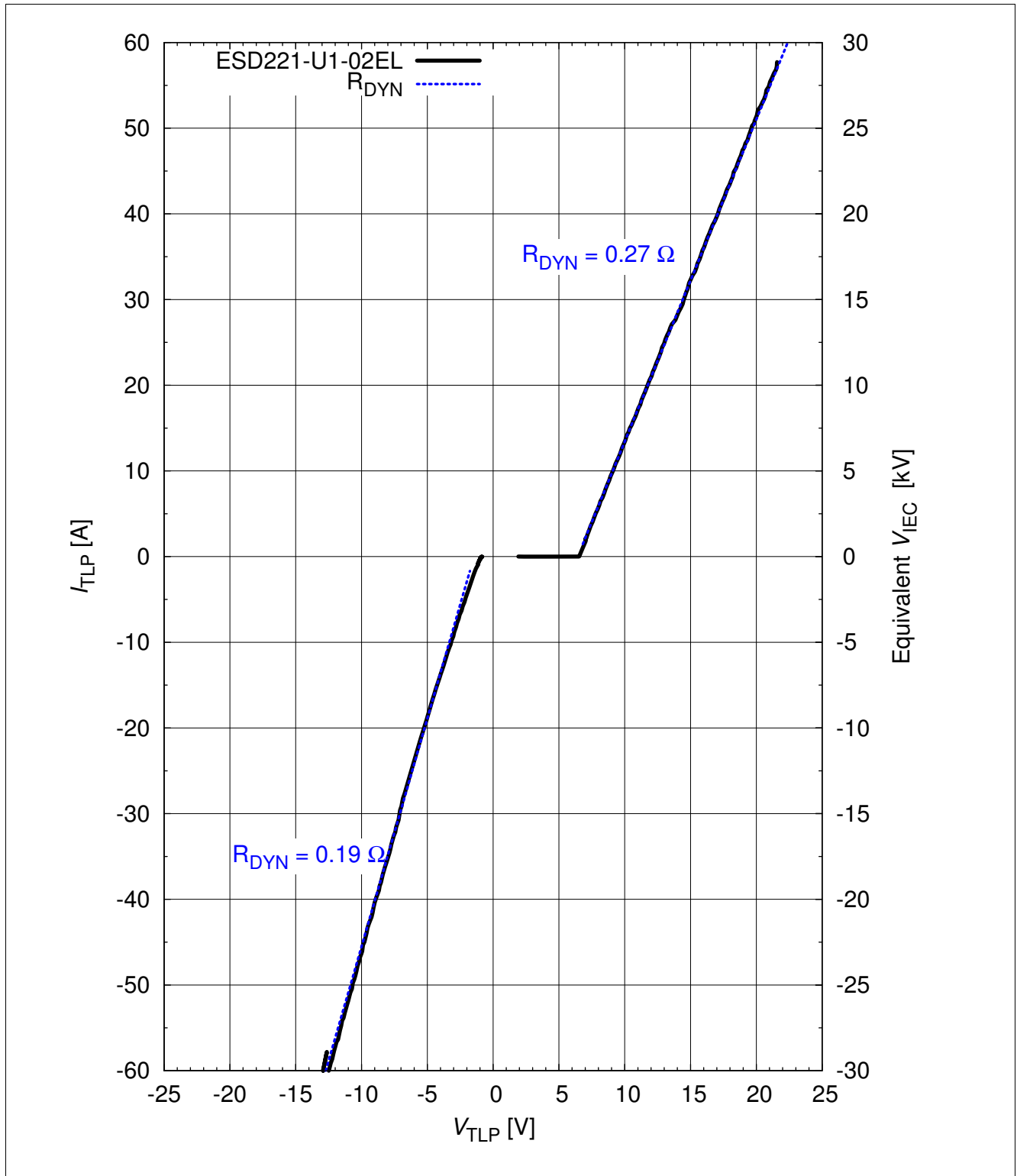


Figure 4-5 Clamping voltage (TLP):  $I_{TLP} = f(V_{TLP})$  [1], pin 1 to pin 2

# Typical Characteristics Diagrams

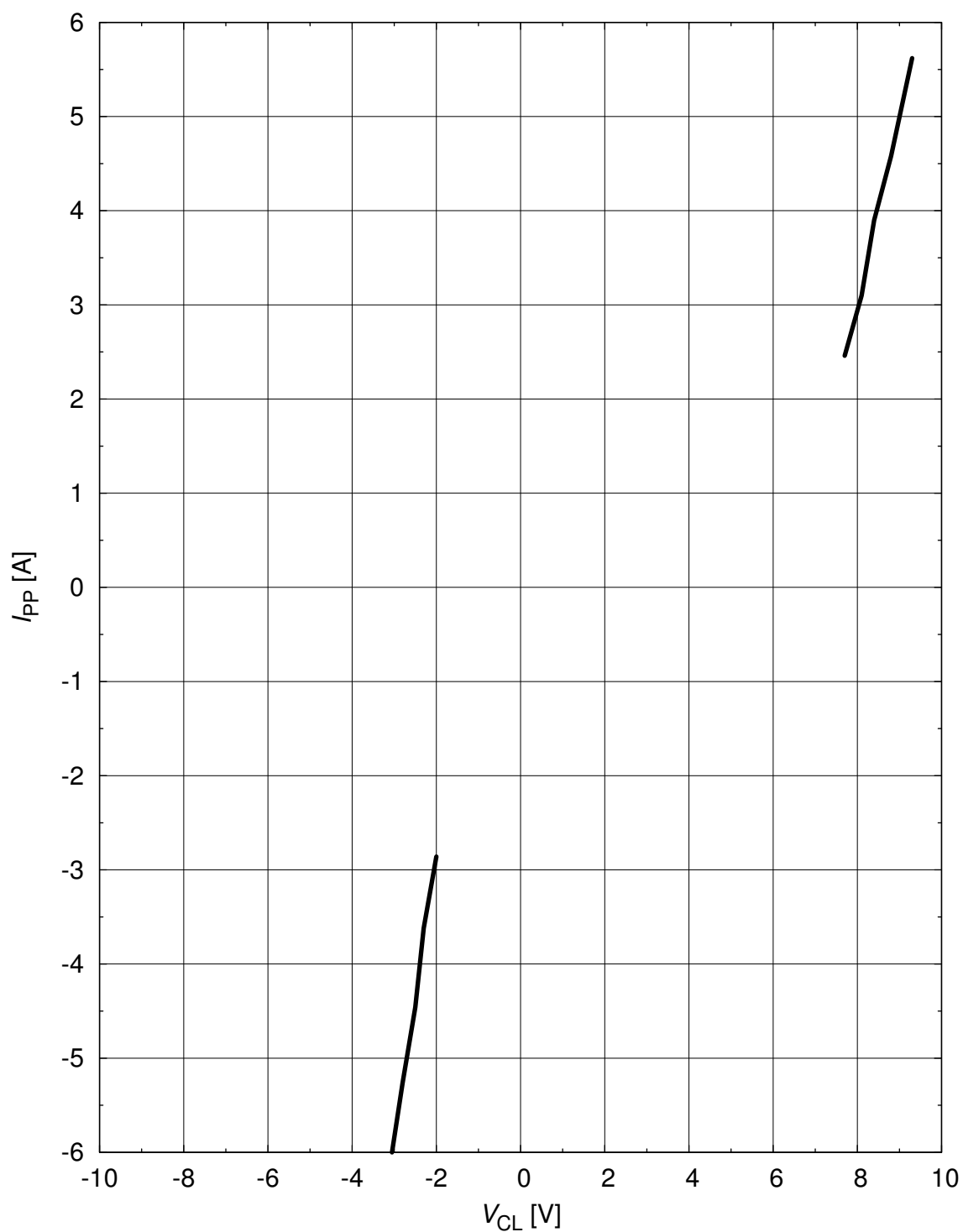


Figure 4-6 Clamping voltage (Surge):  $I_{PP} = f(V_{CL})$  [1], pin 1 to pin 2

Typical Characteristics Diagrams

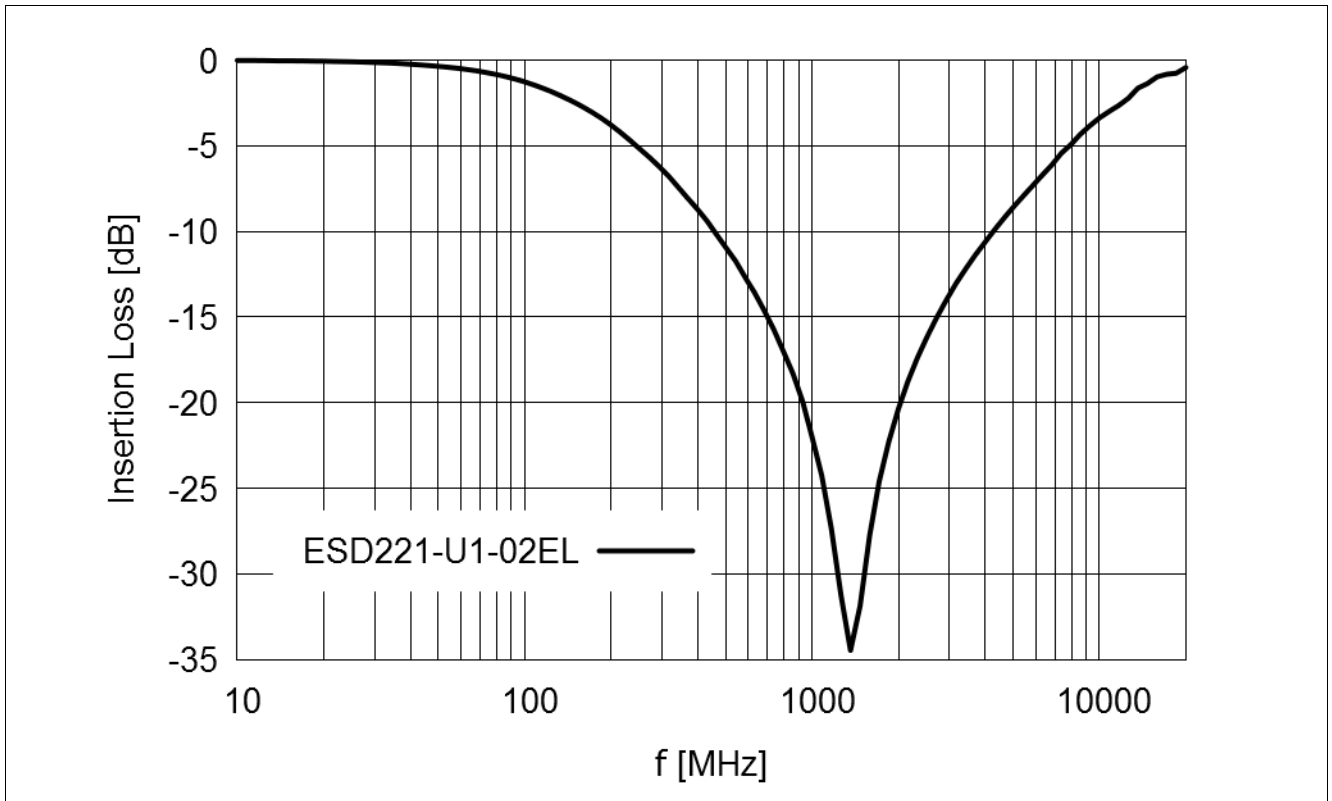
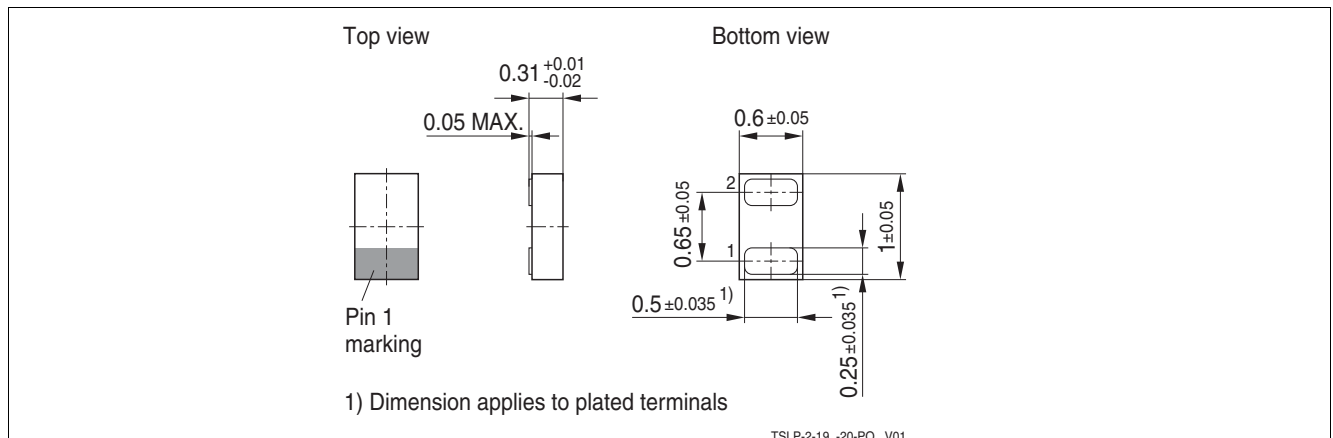


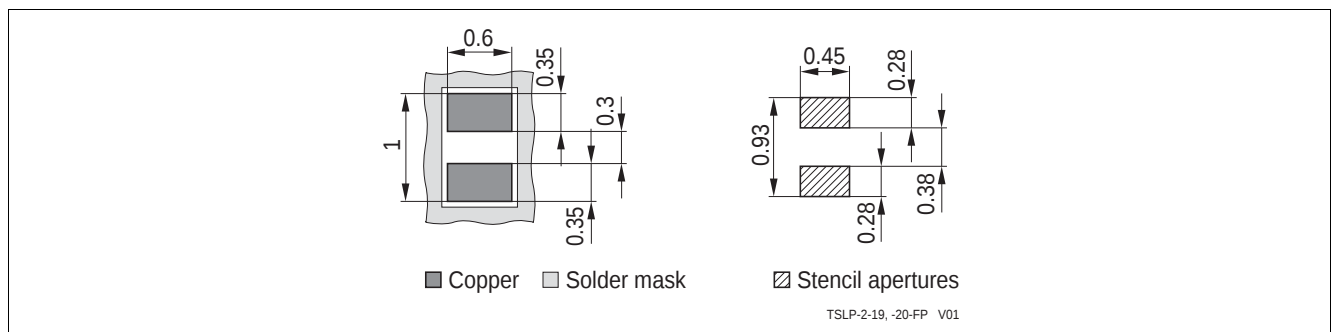
Figure 4-7 Insertion loss vs. frequency in a 50  $\Omega$  system

## 5 Package Information

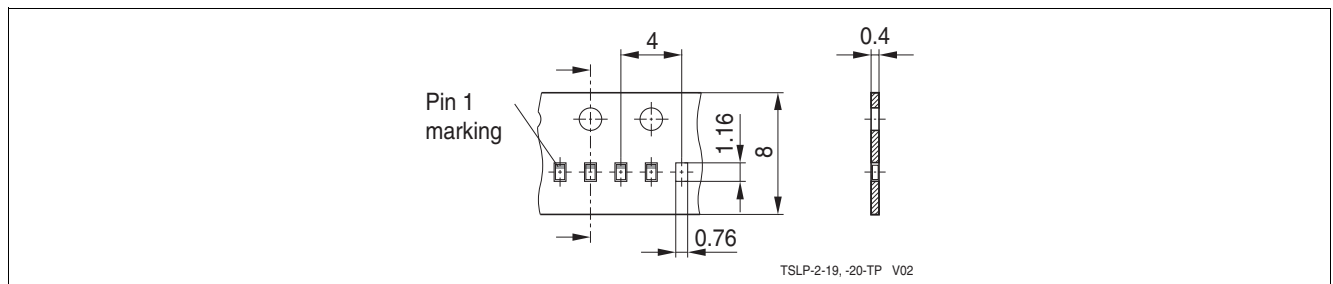
### 5.1 TSLP-2-19



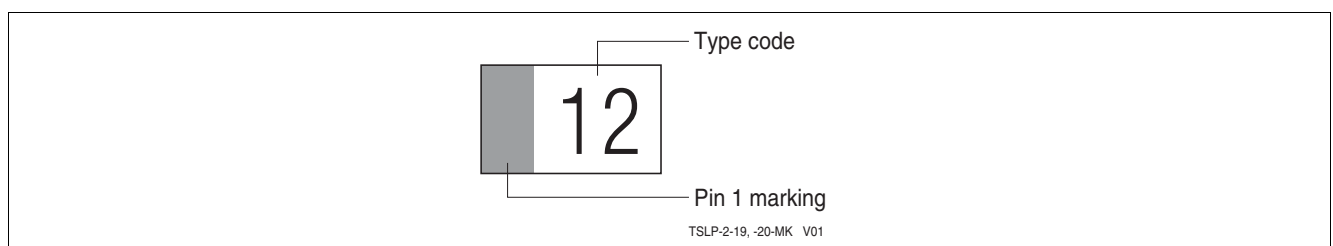
**Figure 5-1 TSLP-2-19: Package outline**



**Figure 5-2 TSLP-2-19: Footprint**



**Figure 5-3 TSLP-2-19: Packing**



**Figure 5-4 TSLP-2-19: Marking example, Type code see: [Table 1-1 "Part Information" on Page 3](#)**

## References

- [1] Infineon AG - **Application Note AN210**: Effective ESD Protection design at System Level Using VF-TLP Characterization Methodology
- [2] Infineon AG - Recommendations for PCB Assembly of Infineon TSLP and TSSLP Packages

## Revision History

| Page or Item                    | Subjects (major changes since previous revision) |
|---------------------------------|--------------------------------------------------|
| <b>Revision 1.0, 2014-05-20</b> |                                                  |
| 5                               | Update of Table 2-2)                             |
|                                 |                                                  |
|                                 |                                                  |
|                                 |                                                  |
|                                 |                                                  |

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